

NCE N-Channel Super Trench Power MOSFET

Description

The NCEP85T16 uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{\text{DS}(\text{ON})}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

General Features

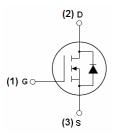
- $V_{DS} = 85V, I_D = 160A$ $R_{DS(ON)} < 3.8 m\Omega @ V_{GS} = 10V$
- Excellent gate charge x R_{DS(on)} product
- Very low on-resistance R_{DS(on)}
- 175 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

100% UIS TESTED!

100% ΔVds TESTED!



Schematic diagram



Marking and pin assignment



TO-220-3L top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP85T16	NCEP85T16	TO-220-3L	-	-	-

Absolute Maximum Ratings (T_c=25 ℃ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	VDS	85	V
Gate-Source Voltage	V _G s	±20	V
Drain Current-Continuous	I _D	160	А
Drain Current-Continuous(T _C =100°C)	I _D (100℃)	112	Α
Pulsed Drain Current	I _{DM}	480	Α
Maximum Power Dissipation	P _D	220	W
Derating factor		1.5	W/℃
Single pulse avalanche energy (Note 5)	E _{AS}	1440	mJ
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 175	$^{\circ}$



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NCEP85T16

Thermal Characteristic

Thermal Resistance,Junction-to-Case ^(Note 2)	R _{θJC}	0.6	°C/W	
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Electrical Characteristics (T_C=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics	·					
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	85		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =85V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	2.5		4.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =80A	-	3.1	3.8	mΩ
Forward Transconductance	g Fs	V _{DS} =10V,I _D =80A	75	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{lss}	\/ -40\/\/ -0\/	-	8500	-	PF
Output Capacitance	C _{oss}	V_{DS} =40V, V_{GS} =0V, F=1.0MHz	-	1520	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.UIVIHZ	-	81	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}		-	30.5	-	nS
Turn-on Rise Time	t _r	V_{DD} =40V, I_D =80A	-	29	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10 V , R_{G} =4.7 Ω	-	95	-	nS
Turn-Off Fall Time	t _f		-	34.5	-	nS
Total Gate Charge	Qg	\/ 40\/ L 00 A	-	105		nC
Gate-Source Charge	Q _{gs}	$V_{DS}=40V, I_{D}=80A,$	-	39		nC
Gate-Drain Charge	Q_{gd}	V _{GS} =10V	-	28		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	V _{GS} =0V,I _S =160A	-		1.2	V
Diode Forward Current (Note 2)	Is		-	-	160	Α
Reverse Recovery Time	t _{rr}	$T_J = 25^{\circ}C$, $I_F = I_S$	-	95		nS
Reverse Recovery Charge	Qrr	$di/dt = 100A/\mu s^{(Note3)}$	_	225		nC

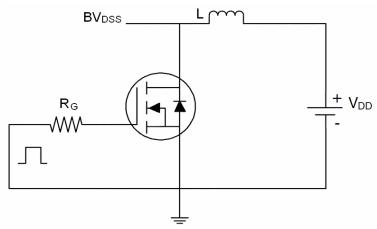
Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition : Tj=25 $^{\circ}\text{C}$,V $_{DD}$ =42.5 V ,V $_{G}$ =10 V ,L=0.5 mH ,Rg=25 Ω

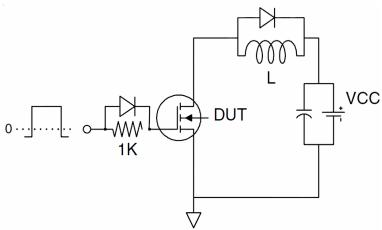


Test Circuit

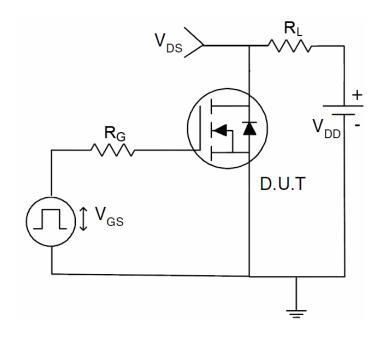
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit





Typical Electrical and Thermal Characteristics

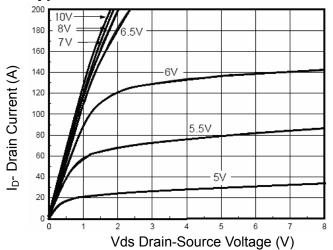


Figure 1 Output Characteristics

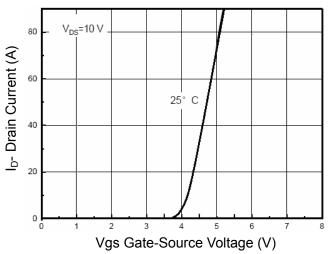


Figure 2 Transfer Characteristics

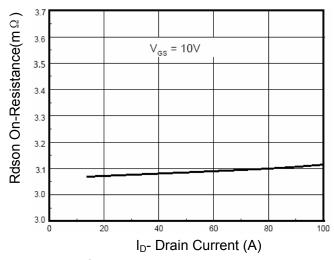


Figure 3 Rdson- Drain Current

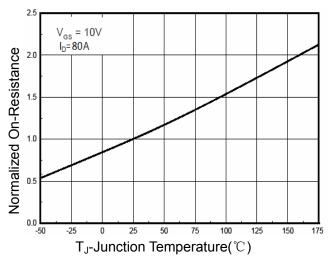


Figure 4 Rdson-JunctionTemperature

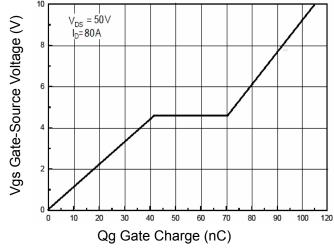


Figure 5 Gate Charge

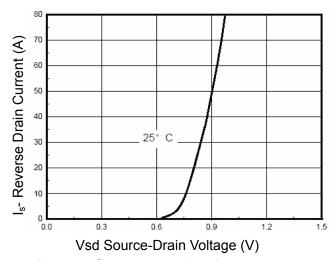
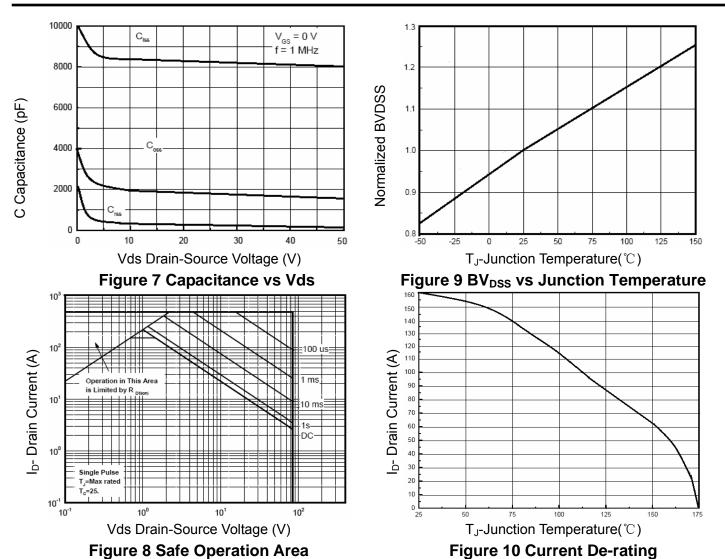


Figure 6 Source- Drain Diode Forward





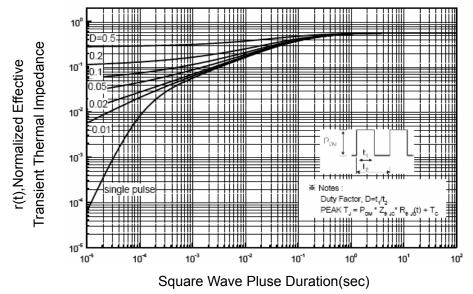


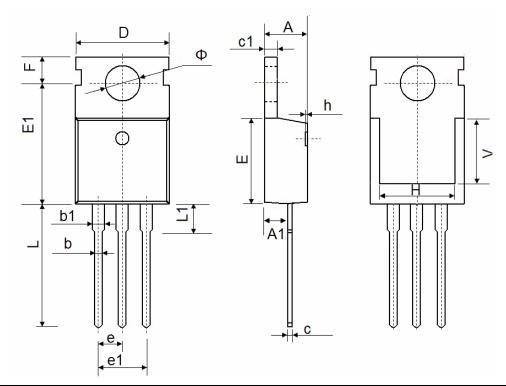
Figure 11 Normalized Maximum Transient Thermal Impedance

Pb Free Product



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TO-220-3L Package Information



Symbol	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	4.400	4.600	0.173	0.181	
A1	2.250	2.550	0.089	0.100	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.330	0.650	0.013	0.026	
c1	1.200	1.400	0.047	0.055	
D	9.910	10.250	0.390	0.404	
E	8.9500	9.750	0.352	0.384	
E1	12.650	12.950	0.498	0.510	
е	2.54	40 TYP. 0.100 TYP.		TYP.	
e1	4.980	5.180	0.196	0.204	
F	2.650	2.950	0.104	0.116	
Н	7.900	8.100	0.311	0.319	
h	0.000	0.300	0.000	0.012	
L	12.900	13.400	0.508	0.528	
L1	2.850	3.250	0.112	0.128	
V	7.50	0 REF.	0.295	REF.	
Ф	3.400	3.800	0.134	0.150	



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